

**SH8M24** 

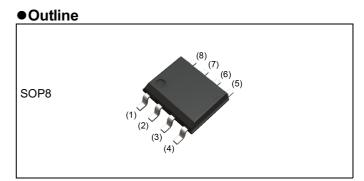
| Symbol                     | Tr1:Nch | Tr2:Pch |
|----------------------------|---------|---------|
| V <sub>DSS</sub>           | 45V     | -45V    |
| R <sub>DS(on)</sub> (Max.) | 46mΩ    | 63mΩ    |
| I <sub>D</sub>             | ±6A     | ±6A     |
| P <sub>D</sub>             | 3.1     | W       |

#### Features

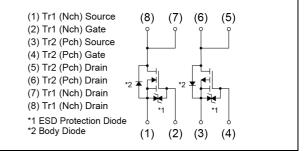
- 1) Low on resistance.
- 2) Small Surface Mount Package (SOP8).
- 3) Pb-free lead plating ; RoHS compliant.
- 4) Halogen Free.

Application

Switching



#### Inner circuit



#### Packaging specifications

|      | Packing                   | Embossed<br>Tape |
|------|---------------------------|------------------|
|      | Reel size (mm)            | 330              |
| Туре | Tape width (mm)           | 12               |
|      | Basic ordering unit (pcs) | 2500             |
|      | Taping code               | ТВ               |
|      | Marking                   | SH8M24           |

## ● Absolute maximum ratings (T<sub>a</sub> = 25°C ,unless otherwise specified)

| Doromo   | tor   | Symbol                       | Va      | lue     | Linit |
|--|-------|------------------------------|---------|---------|-------|
| Parameter  |       | Symbol                       | Tr1:Nch | Tr2:Pch | Unit  |
| Drain - Source voltage                           |       | V <sub>DSS</sub>             | 45      | -45     | V     |
| Continuous drain current                         |       | I <sub>D</sub> *1            | ±6      | ±6      | А     |
| Pulsed drain current                             |       | ۱ <sub>DP</sub> *2           | ±18     | ±14     | А     |
| Gate - Source voltage                            |       | V <sub>GSS</sub>             | ±20     | ±20     | V     |
|  |       | P <sub>D</sub> <sup>*1</sup> | 3       | .1      |       |
| Power dissipation                                | total | P <sub>D</sub> *3            | 2       | .0      | W     |
|  |       | P <sub>D</sub> <sup>*4</sup> | 1       | .4      |       |
| Junction temperature                             |       | Tj                           | 1       | 50      | °C    |
| Operating junction and storage temperature range |       | T <sub>stg</sub>             | -55 to  | +150    | C°    |

#### •Thermal resistance

| Deremeter                              |       | Currence of     |      | Values |      | Linit |
|--|-------|-----------------|------|--------|------|-------|
| Parameter                              |       | Symbol          | Min. | Тур.   | Max. | Unit  |
| Thermal registeres junction embient    | totol | $R_{thJA}^{*3}$ | -    | -      | 62.5 | °C/W  |
| Thermal resistance, junction - ambient | total | $R_{thJA}^{*4}$ | -    | -      | 89.2 | C/VV  |

## •Electrical characteristics (T<sub>a</sub> = 25°C)

| Devenueter               | Currente e l           | T    | Canditiana                                      | Values |                       |      | l lusit |
|--------------------------|------------------------|------|---|--------|-----------------------|------|---------|
| Parameter                | Symbol                 | Туре | Conditions                                      | Min.   | Тур.                  | Max. | Unit    |
| Drain - Source breakdown | V                      | Tr1  | V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA      | 45     | -                     | -    | N       |
| voltage                  | V <sub>(BR)DSS</sub>   | Tr2  | V <sub>GS</sub> = 0V, I <sub>D</sub> = -1mA     | -45    | -                     | -    | V       |
| Breakdown voltage        | ΔV <sub>(BR)DSS</sub>  | Tr1  | $I_D = 1$ mA, referenced to 25°C                | -      | 46.8                  | -    | m) //ºO |
| temperature coefficient  | $\Delta T_j$           | Tr2  | $I_D = -1 \text{ mA}$ , referenced to 25°C      | -      | -50                   | -    | mV/°C   |
| Zero gate voltage        |                        | Tr1  | V <sub>DS</sub> = 45V, V <sub>GS</sub> = 0V     | -      | -                     | 1    |         |
| drain current            | I <sub>DSS</sub>       | Tr2  | V <sub>DS</sub> = -45V, V <sub>GS</sub> = 0V    | -      | -                     | -1   | μA      |
| Gate - Source            |                        | Tr1  | $V_{DS}$ = 0V, $V_{GS}$ = ±20V                  | -      | -                     | ±10  |         |
| leakage current          | I <sub>GSS</sub>       | Tr2  | V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V    | -      | -                     | ±10  | μA      |
| Gate threshold           | V                      | Tr1  | V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA     | 1.0    | .0 - 2.5 V<br>.02.5 V | N    |         |
| voltage                  | V <sub>GS(th)</sub>    | Tr2  | V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA   | -1.0   | -                     | -2.5 | V       |
| Gate threshold voltage   | $\Delta V_{GS(th)}$    | Tr1  | I <sub>D</sub> = 1mA, referenced to 25°C        | -      | -3.9                  | -    | mV/°C   |
| temperature coefficient  | $\Delta T_j$           | Tr2  | $I_D = -1 \text{ mA}$ , referenced to 25°C      | -      | 3.3                   | -    | mv/ C   |
|                          |                        |      | V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A    | -      | 33                    | 46   |         |
|                          |                        | Tr1  | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.5A   | -      | 41                    | 57   |         |
| Static drain - source    | D *5                   |      | V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 4.5A   | I      | 46                    | 64   |         |
| on - state resistance    | R <sub>DS(on)</sub> *5 |      | V <sub>GS</sub> = -10V, I <sub>D</sub> = -3.5A  | -      | 45                    | 63   | mΩ      |
|                          |                        | Tr2  | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.5A | -      | 60                    | 84   |         |
|                          |                        |      | V <sub>GS</sub> = -4.0V, I <sub>D</sub> = -3.5A | -      | 66                    | 92   |         |
| Cata registeres          | D                      | Tr1  | f-1MHz anan drain                               | -      | 5.0                   | -    | Ω       |
| Gate resistance          | R <sub>G</sub>         | Tr2  | f=1MHz, open drain                              | -      | 6.0                   | -    | 12      |
| Forward Transfer         | Y <sub>fs</sub>  *5    | Tr1  | V <sub>DS</sub> = 10V, I <sub>D</sub> = 4.5A    | 3.5    | -                     | -    | S       |
| Admittance               |                        | Tr2  | V <sub>DS</sub> = -10V, I <sub>D</sub> = -3.5A  | 4.5    | -                     | -    | 3       |

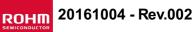
\*1 Pw  $\leq$  1s, Mounted on a ceramic board (30×30×0.8mm), Limited only by maximum temperature allowed.

\*2 Pw  $\leq 10\mu$ s, Duty cycle  $\leq 1\%$ 

\*3 Mounted on a ceramic board (30×30×0.8mm)

\*4 Mounted on a FR4 (25×25×0.8mm)

\*5 Pulsed



## • Electrical characteristics ( $T_a = 25^{\circ}C$ )

<Tr1>

| Deremeter                    | Cump of                | Conditions                            |      | Unit |      |      |
|------------------------------|------------------------|---------------------------------------|------|------|------|------|
| Parameter                    | Symbol                 | Conditions                            | Min. | Тур. | Max. | Unit |
| Input capacitance            | C <sub>iss</sub>       | V <sub>GS</sub> = 0V                  | -    | 550  | -    |      |
| Output capacitance           | C <sub>oss</sub>       | V <sub>DS</sub> = 10V                 | -    | 140  | -    | pF   |
| Reverse transfer capacitance | C <sub>rss</sub>       | f = 1MHz                              | -    | 70   | -    |      |
| Turn - on delay time         | t <sub>d(on)</sub> *5  | $V_{DD} \simeq 25 V$ , $V_{GS}$ = 10V | -    | 12   | -    |      |
| Rise time                    | t <sub>r</sub> *5      | I <sub>D</sub> = 2.5A                 | -    | 18   | -    | 20   |
| Turn - off delay time        | t <sub>d(off)</sub> *5 | R <sub>L</sub> = 10Ω                  | -    | 42   | -    | ns   |
| Fall time                    | $t_{f}^{*5}$           | R <sub>G</sub> = 10Ω                  | -    | 12   | -    |      |

#### <Tr2>

| Parameter                    | Symbol Conditions |                                       | ,    | Unit |      |      |
|------------------------------|-------------------|---------------------------------------|------|------|------|------|
| Parameter                    | Symbol            | Conditions                            | Min. | Тур. | Max. | Unit |
| Input capacitance            | C <sub>iss</sub>  | V <sub>GS</sub> = 0V                  | -    | 1700 | -    |      |
| Output capacitance           | C <sub>oss</sub>  | V <sub>DS</sub> = -10V                | -    | 200  | -    | pF   |
| Reverse transfer capacitance | C <sub>rss</sub>  | f = 1MHz                              | -    | 135  | -    |      |
| Turn - on delay time         | $t_{d(on)}$ *5    | $V_{DD} \simeq$ -25V, $V_{GS}$ = -10V | -    | 16   | -    |      |
| Rise time                    | t <sub>r</sub> *5 | I <sub>D</sub> = -2.0A                | -    | 17   | -    | 20   |
| Turn - off delay time        | $t_{d(off)}$ *5   | R <sub>L</sub> = 12.4Ω                | -    | 70   | -    | ns   |
| Fall time                    | t <sub>f</sub> *5 | R <sub>G</sub> = 10Ω                  | -    | 14   | -    |      |



## • Gate charge characteristics ( $T_a = 25^{\circ}C$ )

#### <Tr1>

| Deremeter            | Sumbol            | Conditions   | Values |      |      |      |
|----------------------|-------------------|--|--------|------|------|------|
| Parameter            | Symbol            | Conditions   | Min.   | Тур. | Max. | Unit |
| Total gate charge    | Q <sub>g</sub> *5 |  | -      | 6.8  | 9.6  |      |
| Gate - Source charge | $Q_{gs}^{*5}$     | V <sub>DD</sub> ≃ 25V, I <sub>D</sub> = 6A<br>V <sub>GS</sub> = 5V | -      | 2.0  | -    | nC   |
| Gate - Drain charge  | $Q_{gd}^{*5}$     |  | -      | 2.9  | -    |      |

#### <Tr2>

| Deremeter            | Cumphal             | Conditions  |      | Values |      | Linit |
|----------------------|---------------------|---|------|--------|------|-------|
| Parameter            | Symbol Conditions – |   | Min. | Тур.   | Max. | Unit  |
| Total gate charge    | $Q_g^{*5}$          |   | -    | 13     | 18.2 |       |
| Gate - Source charge | Q <sub>gs</sub> *5  | V <sub>DD</sub> ≃ -25V, I <sub>D</sub> = -3.5A<br>V <sub>GS</sub> = -5V | -    | 3.6    | -    | nC    |
| Gate - Drain charge  | $Q_{gd}^{*5}$       |   | -    | 4.7    | -    |       |

## •Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

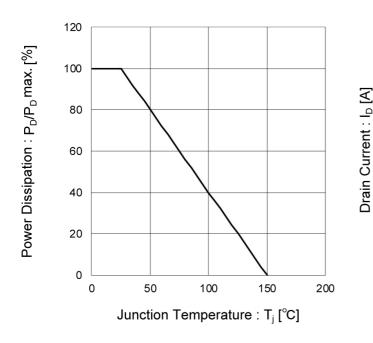
#### <Tr1>

| Deremeter                  | Cumphal             | Conditions                                  | ,    | Values |      | Linit |
|----------------------------|---------------------|---|------|--------|------|-------|
| Parameter                  | Symbol Conditions – |   | Min. | Тур.   | Max. | Unit  |
| Continuous forward current | ا <sub>S</sub>      | T - 25°0                                    | -    | -      | 1.66 | ^     |
| Pulse forward current      | I <sub>SP</sub> *2  | T <sub>a</sub> = 25°C                       | -    | -      | 18   | A     |
| Forward voltage            | $V_{SD}^{*5}$       | V <sub>GS</sub> = 0V, I <sub>S</sub> = 4.5A | -    | -      | 1.2  | V     |

#### <Tr2>

| Deremeter                  | Sumbol             | Conditions                                   | ,    | Values |       | Linit |
|----------------------------|--------------------|--|------|--------|-------|-------|
| Parameter                  | Symbol Conditions  | Min.   | Тур. | Max.   | Unit  |       |
| Continuous forward current | ا <sub>s</sub>     | T - 25°0                                     | -    | -      | -1.66 | ^     |
| Pulse forward current      | ا <sub>SP</sub> *2 | T <sub>a</sub> = 25°C                        | -    | -      | -14   | A     |
| Forward voltage            | $V_{SD}^{*5}$      | V <sub>GS</sub> = 0V, I <sub>S</sub> = -3.5A | -    | -      | -1.2  | V     |

#### •Electrical characteristic curves <Tr1>



#### Fig.1 Power Dissipation Derating Curve

100 Operation in this area is limited by R<sub>DS</sub>(on)( V<sub>GS</sub> = 10V ) 10  $P_W = 100 \mu s$ 1 P<sub>W</sub> = 1ms 1111 DC Operation  $P_W = 10ms$ 0.1 T<sub>a</sub>=25°C 0.01 Single Pulse Mounted on a ceramic board (30mm × 30mm × 0.8mm) 0.001 0.1 10 100 1 Drain - Source Voltage : V<sub>DS</sub> [V]

#### Fig.2 Maximum Safe Operating Area

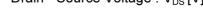
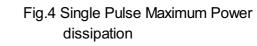
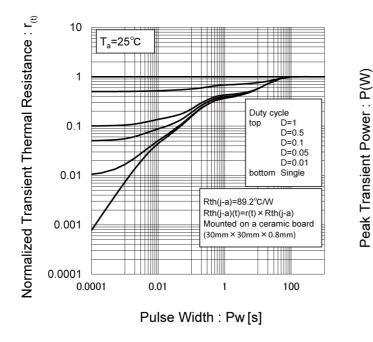
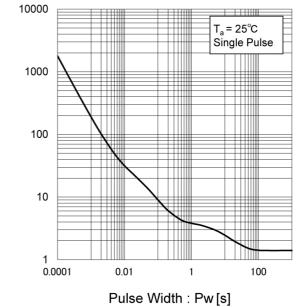


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

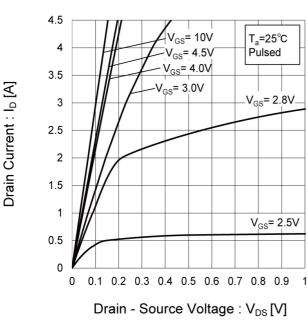












#### Fig.5 Typical Output Characteristics(I)

Fig.6 Typical Output Characteristics(II)

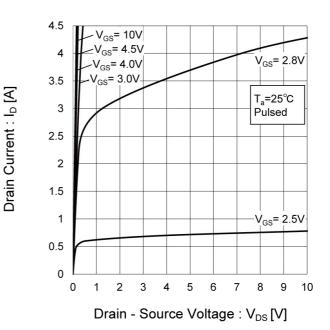
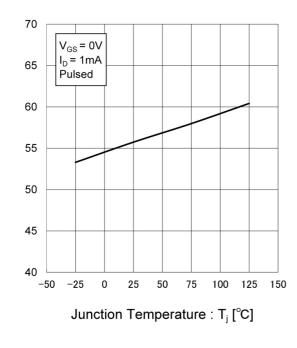


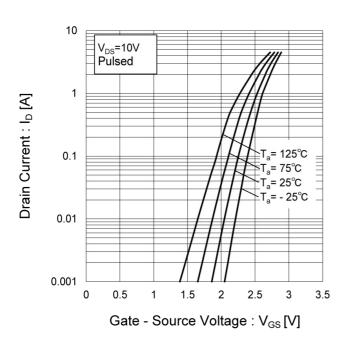
Fig.7 Breakdown Voltage vs. Junction Temperature





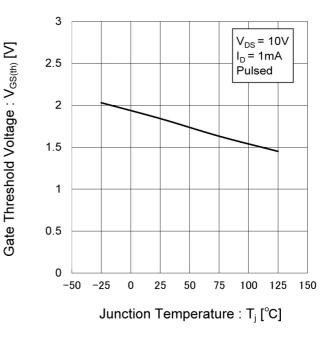


#### •Electrical characteristic curves <Tr1>

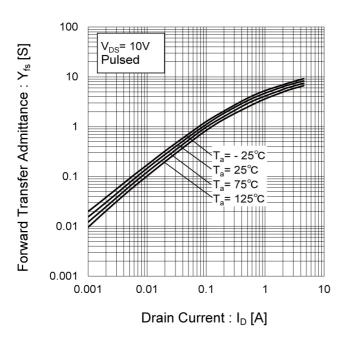


## Fig.8 Typical Transfer Characteristics

Fig.9 Gate Threshold Voltage vs. Junction Temperature



# Fig.10 Forward Transfer Admittance vs. Drain Current





#### •Electrical characteristic curves <Tr1>

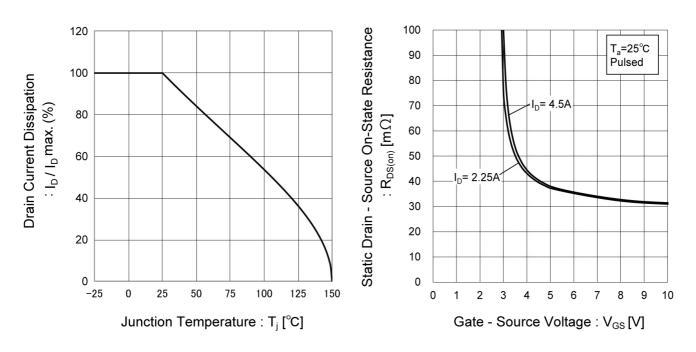


Fig.11 Drain Current Derating Curve

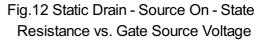
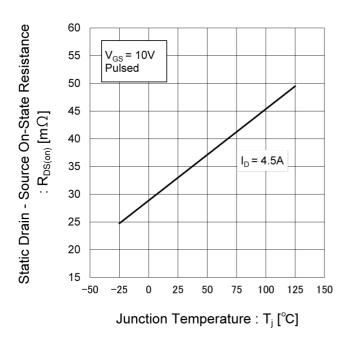


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature





#### • Electrical characteristic curves < Tr1>

Fig.14 Static Drain - Source On - State

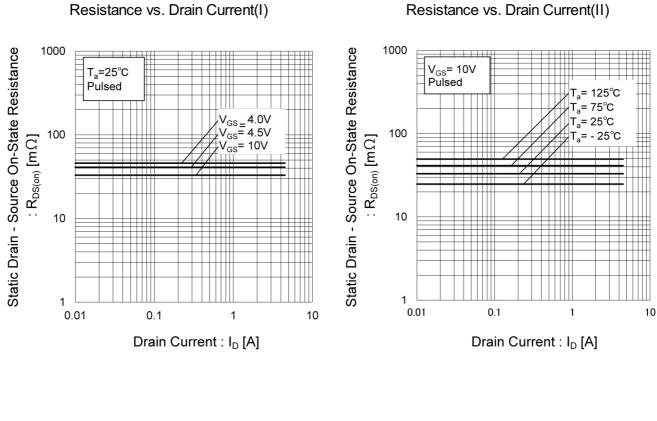
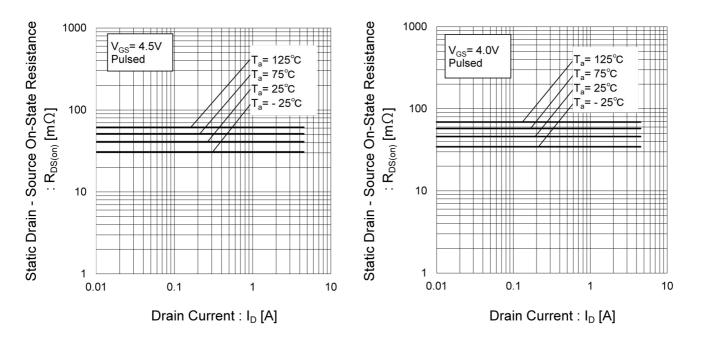


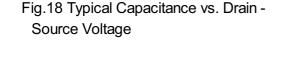
Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III) Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

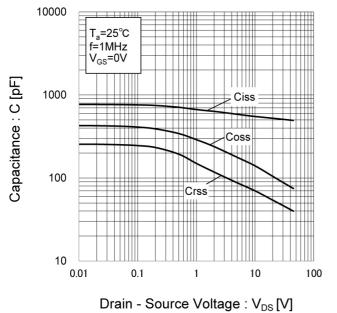
Fig.15 Static Drain - Source On - State

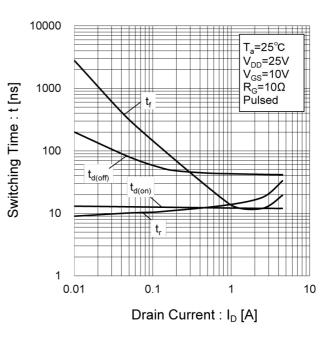




#### • Electrical characteristic curves <Tr1>







#### Fig.19 Switching Characteristics

Fig.20 Dynamic Input Characteristics

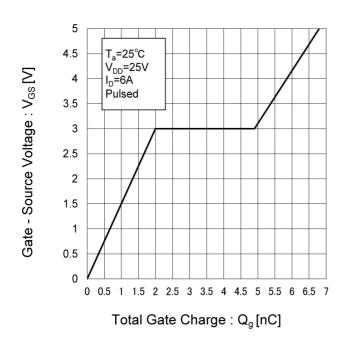
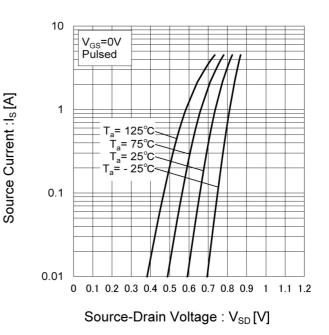
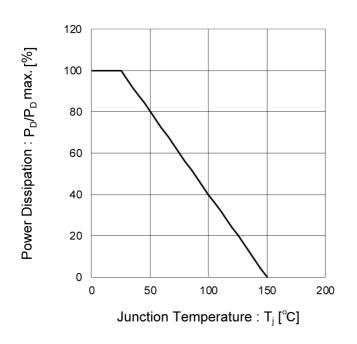


Fig.21 Source Current vs. Source Drain Voltage





#### Electrical characteristic curves <Tr2>



#### Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

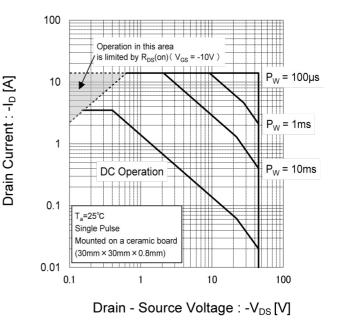
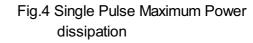
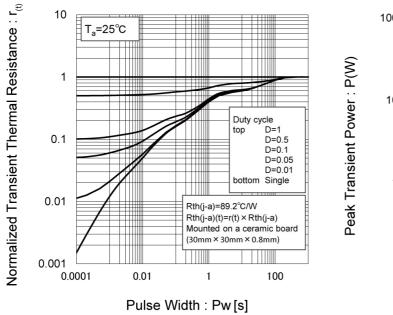
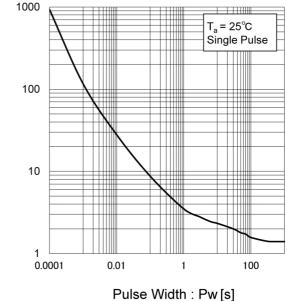


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

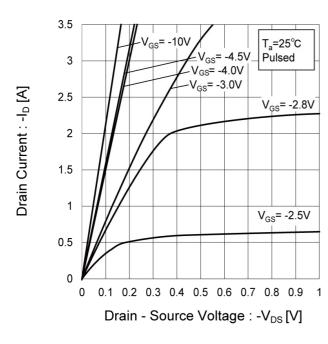












#### Fig.5 Typical Output Characteristics(I)

3.5 - V<sub>GS</sub>= -10V V<sub>GS</sub>= -4.5V T<sub>a</sub>=25°C 3 Pulsed V<sub>GS</sub>= -4.0V V<sub>GS</sub>= -3.0V 2.5 V<sub>GS</sub>= -2.8V 2 1.5 V<sub>GS</sub>= -2.5V 1 0.5 0 0 2 3 4 5 6 7 8 9 10 1 Drain - Source Voltage : -V<sub>DS</sub> [V]

Drain Current : -I<sub>D</sub> [A]

## Fig.6 Typical Output Characteristics(II)



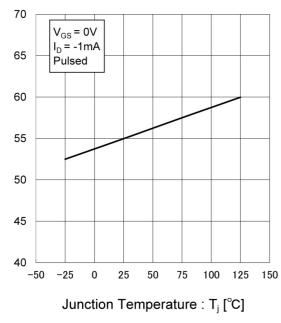
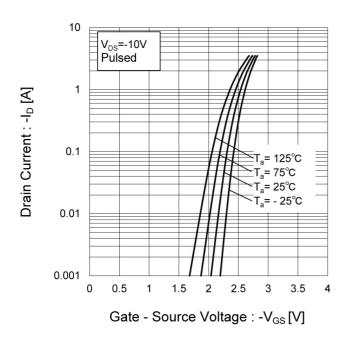


Fig.7 Breakdown Voltage vs. Junction Temperature

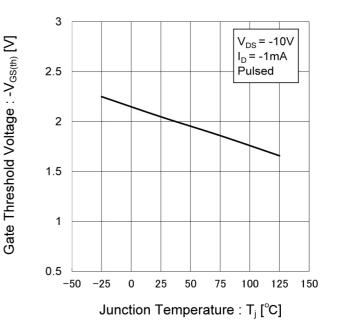


#### •Electrical characteristic curves <Tr2>



## Fig.8 Typical Transfer Characteristics

## Fig.9 Gate Threshold Voltage vs. Junction Temperature



# Fig.10 Forward Transfer Admittance vs. Drain Current

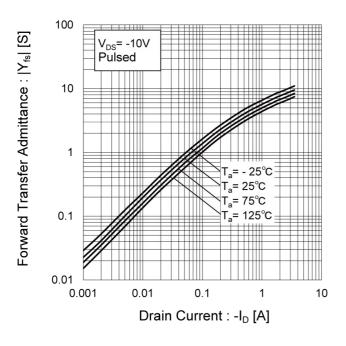
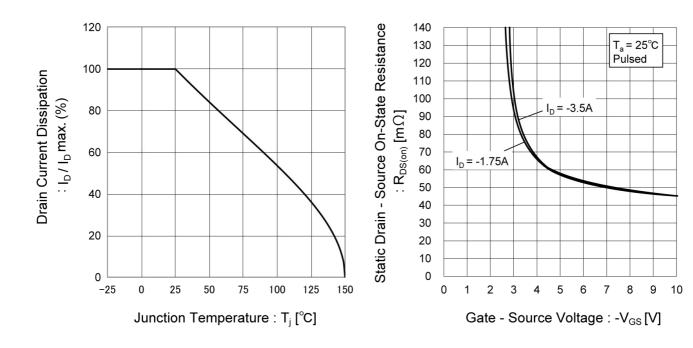




Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

#### •Electrical characteristic curves <Tr2>



#### Fig.11 Drain Current Derating Curve

Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

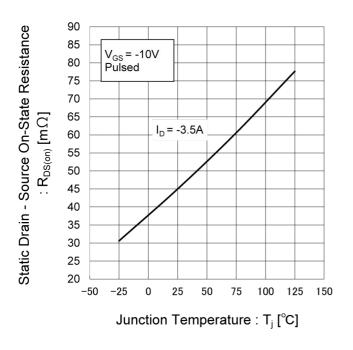


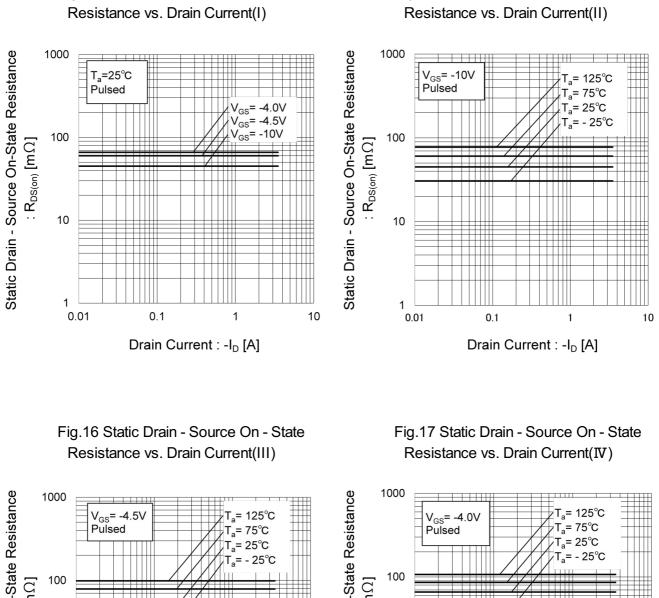


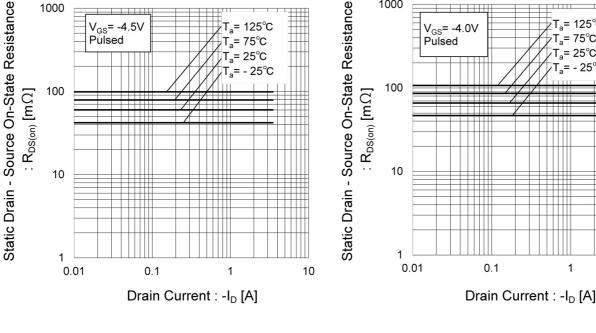


Fig.15 Static Drain - Source On - State

#### • Electrical characteristic curves < Tr2>

Fig.14 Static Drain - Source On - State

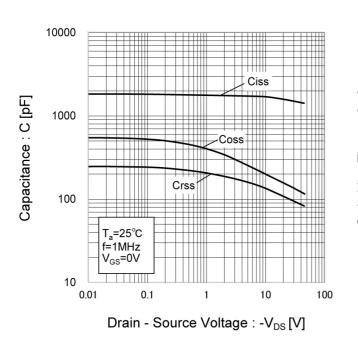






10

#### • Electrical characteristic curves < Tr2>



## Fig.18 Typical Capacitance vs. Drain -Source Voltage

Fig.19 Switching Characteristics

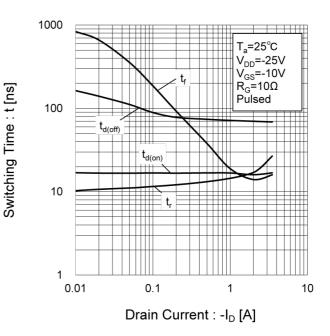


Fig.20 Dynamic Input Characteristics

Gate - Source Voltage : -V<sub>GS</sub> [V]

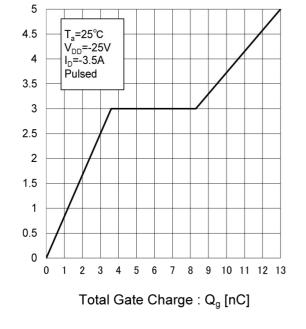
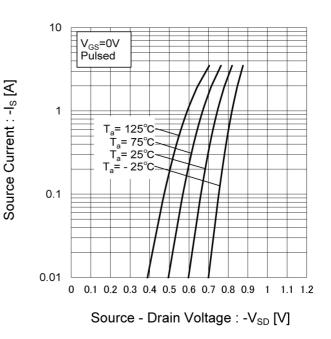


Fig.21 Source Current vs. Source Drain Voltage





#### Measurement circuits <Tr1>

Fig.1-1 Switching Time Measurement Circuit

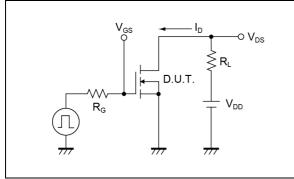


Fig.2-1 Gate Charge Measurement Circuit

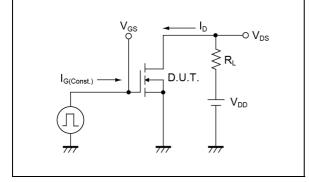
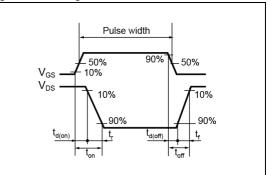
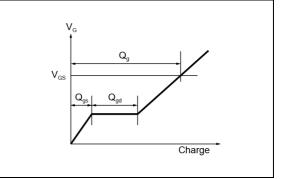


Fig.1-2 Switching Waveforms









## Measurement circuits <Tr2>

Fig.3-1 Switching Time Measurement Circuit

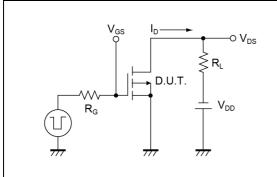


Fig.4-1 Gate Charge Measurement Circuit

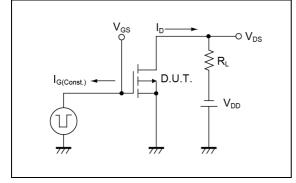
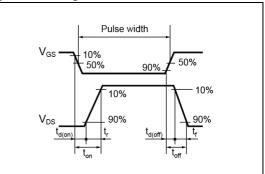
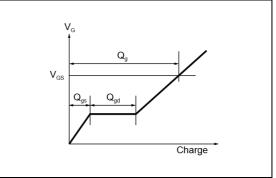


Fig.3-2 Switching Waveforms

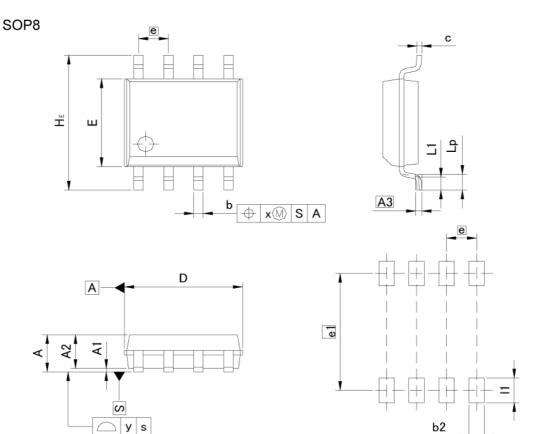








#### Dimensions



Pattern of terminal position areas [Not a pattern of soldering pads]

| DIM | MILIM | IETERS | INC   | HES   |
|-----|-------|--------|-------|-------|
| DIM | MIN   | MAX    | MIN   | MAX   |
| A   | -     | 1.75   | -     | 0.069 |
| A1  | 0     | .15    | 0.0   | 06    |
| A2  | 1.40  | 1.60   | 0.055 | 0.063 |
| A3  | 0     | .25    | 0.0   | 10    |
| b   | 0.30  | 0.50   | 0.012 | 0.020 |
| с   | 0.10  | 0.30   | 0.004 | 0.012 |
| D   | 4.80  | 5.20   | 0.189 | 0.205 |
| E   | 3.75  | 4.05   | 0.148 | 0.159 |
| е   | 1.    | .27    | 0.0   | 50    |
| HE  | 5.70  | 6.30   | 0.224 | 0.248 |
| L1  | 0.40  | 0.60   | 0.016 | 0.024 |
| Lp  | 0.65  | 0.85   | 0.026 | 0.033 |
| х   | 0     | .15    | 0.0   | 06    |
| У   | 0     | .10    | 0.0   | 04    |

| DIM | MILIMETERS  |      | INCHES           |       |
|-----|-------------|------|------------------|-------|
|     | MIN         | MAX  | MIN              | MAX   |
| b2  | <del></del> | 0.65 | -                | 0.026 |
| e1  | 5.15        |      | 0.203            |       |
| 1   | -           | 1.15 | <del>, ,</del> , | 0.045 |

Dimension in mm/inches



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| (Note1) Medical Equipment Classification of the Specific Applications |
|---|
|---|

| JÁPAN  | USA     | EU         | CHINA  |
|--------|---------|------------|--------|
| CLASSⅢ | CLASSⅢ  | CLASS II b | CLASSI |
| CLASSⅣ | CLASSII | CLASSⅢ     |        |

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  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

#### Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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